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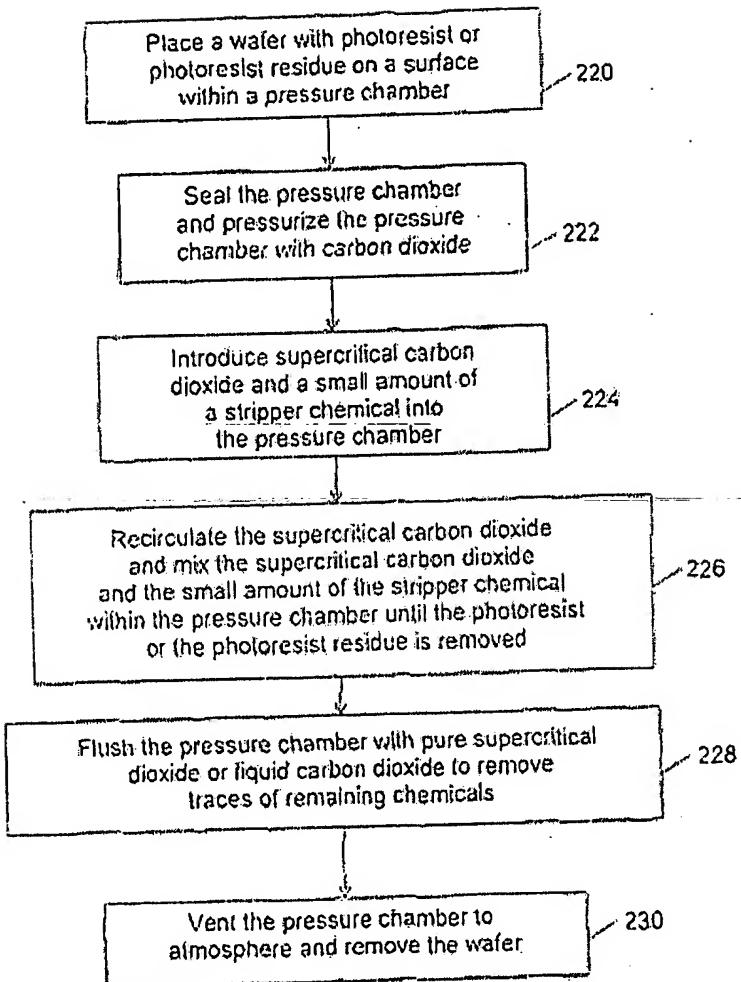
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REMOVAL OF PHOTORESIST AND PHOTORESIST RESIDUE FROM
SEMICONDUCTORS USING SUPERCRITICAL CARBON DIOXIDE
PROCESS

(71)
TOKYO ELECTRON LIMITED Akasaka 5-chome, Minato-ku, Tokyo 107-8481;
(JP). [JP/JP].

(72)



MULLEE, William, H. 10592 S.W. 63rd Drive, Portland, OR 97219; (US).

(74)

HAVERSTOCK, Thomas, B. Haverstock & Owens LLP, Suite 420, 260 Sheridan Avenue, Palo Alto, CA 94306; (US).

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